

GaAs-IR-Lumineszenzdiode in SMT-Gehäuse mit Linse

GaAs Infrared Emitter in SMT Package with lens

SFH 4219



Wesentliche Merkmale

- TOPLED mit Linse
- GaAs-LED mit sehr hohem Wirkungsgrad
- Gute Linearität ($I_e = f[I_F]$) bei hohen Strömen
- Gleichstrom- (mit Modulation) oder Impulsbetrieb möglich
- Hohe Zuverlässigkeit
- Hohe Impulsbelastbarkeit
- Oberflächenmontage geeignet
- Gegurtet lieferbar
- SFH 4219 Gehäusegleich mit SFH 3219

Anwendungen

- Miniaturlichtschranken für Gleich- und Wechsellichtbetrieb, Lochstreifenleser
- Industrieelektronik
- „Messen/Steuern/Regeln“
- Automobiltechnik
- Sensorik
- Alarm- und Sicherungssysteme
- IR-Freiraumübertragung

Features

- TOPLED with lens
- Very highly efficient GaAs-LED
- Good Linearity ($I_e = f[I_F]$) at high currents
- DC (with modulation) or pulsed operations are possible
- High reliability
- High pulse handling capability
- Suitable for surface mounting (SMT)
- Available on tape and reel
- SFH 4219 same package as SFH 3219

Applications

- Miniature photointerrupters
- Industrial electronics
- For drive and control circuits
- Automotive technology
- Sensor technology
- Alarm and safety equipment
- IR free air transmission

Typ Type	Bestellnummer Ordering Code	Gehäuse Package
SFH 4219	Q62702 P5410	Kathodenkennzeichnung: abgesetzte Ecke cathode marking: bevelled edge TOPLED

Grenzwerte ($T_A = 25\text{ °C}$)**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Sperrspannung Reverse voltage	V_R	5	V
Durchlaßstrom Forward current	I_F	100	mA
Stoßstrom, $\tau = 10\text{ }\mu\text{s}$, $D = 0$ Surge current	I_{FSM}	3	A
Verlustleistung Power dissipation	P_{tot}	160	mW
Wärmewiderstand Sperrschicht - Umgebung bei Montage auf FR4 Platine, Padgröße je 16 mm^2 Thermal resistance junction - ambient mounted on PC-board (FR4), padsize 16 mm^2 each	R_{thJA}	450	K/W
Wärmewiderstand Sperrschicht - Lötstelle bei Montage auf Metall-Block Thermal resistance junction - soldering point, mounted on metal block	R_{thJS}	200	K/W

Kennwerte ($T_A = 25\text{ °C}$)**Characteristics**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	λ_{peak}	950	nm
Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} $I_F = 100\text{ mA}$	$\Delta\lambda$	55	nm
Abstrahlwinkel Half angle	φ	± 25	Grad deg.
Aktive Chipfläche Active chip area	A	0.09	mm^2
Abmessungen der aktiven Chipfläche Dimensions of the active chip area	$L \times B$ $L \times W$	0.3×0.3	mm

Kennwerte ($T_A = 25\text{ °C}$)**Characteristics** (cont'd)

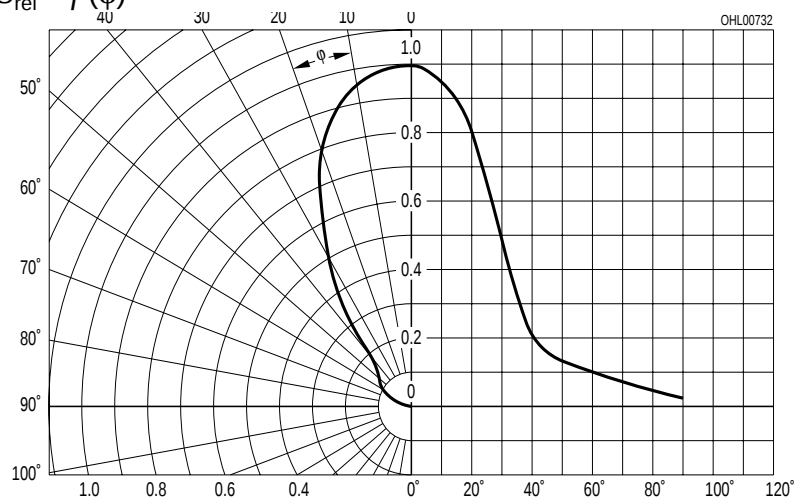
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei $I_F = 100\text{ mA}$, $R_L = 50\text{ }\Omega$ Switching times, I_e from 10% to 90% and from 90% to 10%, $I_F = 100\text{ mA}$, $R_L = 50\text{ }\Omega$	t_r , t_f	0.5	μs
Kapazität, Capacitance $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_o	25	pF
Durchlaßspannung, Forward voltage $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$ $I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	V_F V_F	1.3 (≤ 1.5) 1.9 (≤ 2.5)	V V
Sperrstrom, Reverse current $V_R = 5\text{ V}$	I_R	0.01 (≤ 1)	μA
Gesamtstrahlungsfluß, Total radiant flux $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	Φ_e	14	mW
Temperaturkoeffizient von I_e bzw. Φ_e , $I_F = 100\text{ mA}$ Temperature coefficient of I_e or Φ_e , $I_F = 100\text{ mA}$	TC_I	- 0.55	%/K
Temperaturkoeffizient von V_F , $I_F = 100\text{ mA}$ Temperature coefficient of V_F , $I_F = 100\text{ mA}$	TC_V	- 1.5	mV/K
Temperaturkoeffizient von λ , $I_F = 100\text{ mA}$ Temperature coefficient of λ , $I_F = 100\text{ mA}$	TC_λ	+ 0.3	nm/K

Strahlstärke I_e in Achsrichtunggemessen bei einem Raumwinkel $\Omega = 0.01$ sr**Radiant Intensity I_e in Axial Direction**at a solid angle of $\Omega = 0.01$ sr

Bezeichnung Parameter	Symbol	Werte Values	Einheit Unit
Strahlstärke Radiant intensity $I_F = 100$ mA, $t_p = 20$ ms	$I_{e\min}$ $I_{e\text{typ}}$	4 13	mW/sr mW/sr
Strahlstärke Radiant intensity $I_F = 1$ A, $t_p = 100$ μ s	$I_{e\text{typ}}$	90	mW/sr

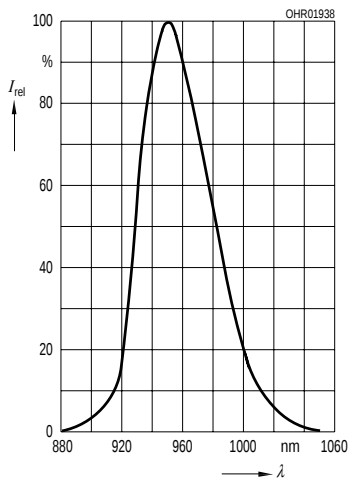
Radiation Characteristics

$$S_{\text{rel}} = f(\varphi)$$



Relative Spectral Emission

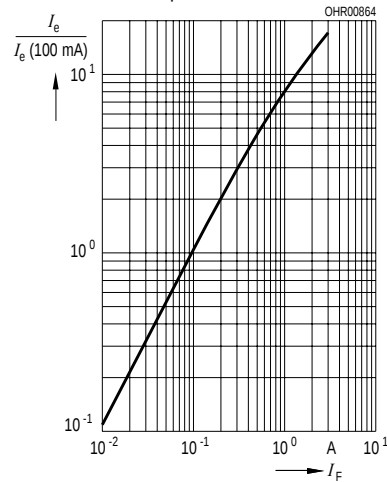
$$I_{\text{rel}} = f(\lambda)$$



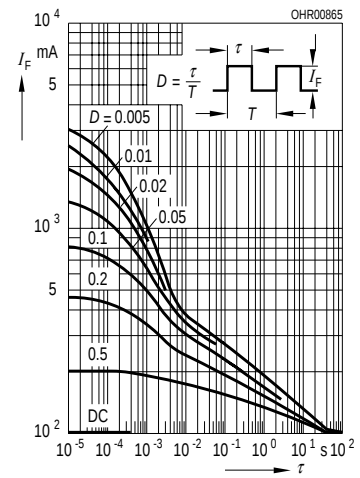
Radiant Intensity

$$\frac{I_e}{I_e 100 \text{ mA}} = f(I_F)$$

Single pulse, $t_p = 20 \mu\text{s}$

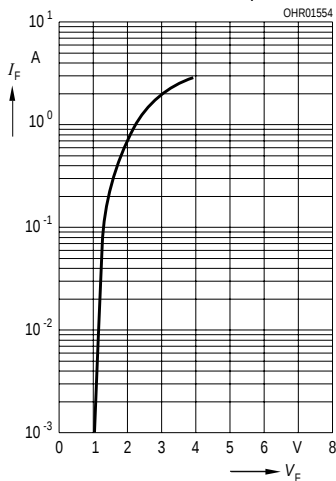


Permissible Pulse Handling Capability $I_F = f(t_p)$, duty cycle $D = \text{parameter}$, $T_A = 20^\circ\text{C}$



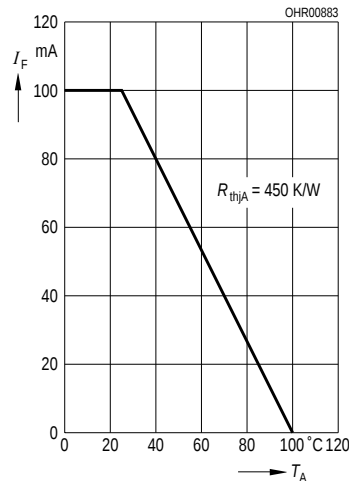
Forward Current

$$I_F = f(V_F), \text{ single pulse, } t_p = 20 \mu\text{s}$$



Max. Permissible Forward Current

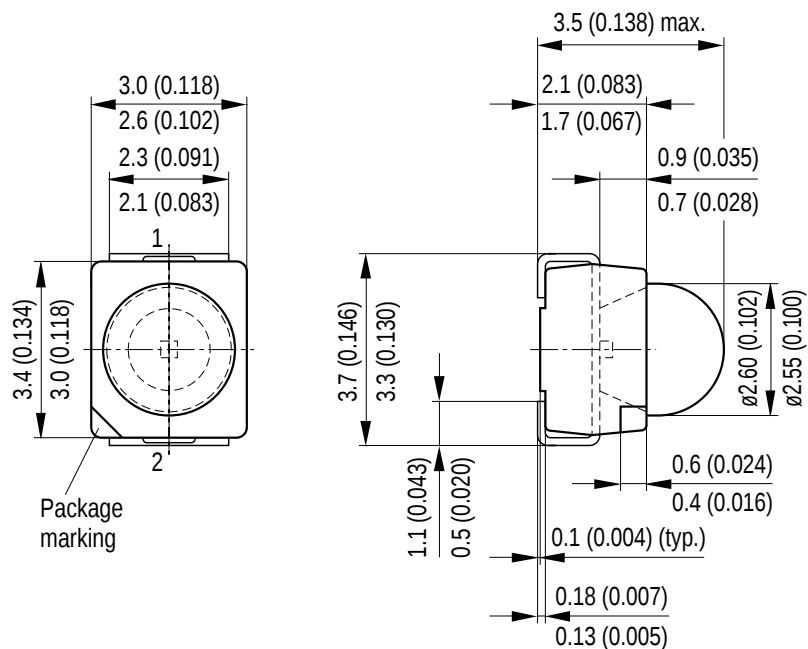
$$I_F = f(T_A)$$



Zusätzliche Informationen über allgemeine Lötbedingungen erhalten Sie auf Anfrage.

For additional information on general soldering conditions please contact us.

Maßzeichnung Package Outlines



GEOY6956

Maße in mm, wenn nicht anders angegeben / Dimensions in mm, unless otherwise specified.

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